



Features

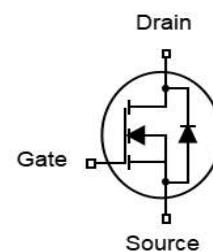
- N-Channel
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 100% EAS Tested

| | | |
|--------------------------------------|-----|------------------|
| V_{DS} | 150 | V |
| $R_{DS(on),TYP}@ V_{GS}=10\text{ V}$ | 7.4 | $\text{m}\Omega$ |
| I_D | 85 | A |

DFN5x6



| Part ID | Package Type | Marking | Packing |
|-------------|--------------|-------------|--------------|
| ZTG088N15GC | DFN5x6 | ZTG088N15GC | 5000pcs/Reel |



Absolute Maximum Ratings $T_A=25^\circ\text{C}$, unless otherwise specified

| Symbol | Parameter | Rating | Unit | |
|--|--|-------------------------|---------------------------|---|
| Common Ratings ($T_c=25^\circ\text{C}$ Unless Otherwise Noted) | | | | |
| V_{GS} | Gate-Source Voltage | ± 20 | V | |
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | 150 | V | |
| T_J | Maximum Junction Temperature | 150 | $^\circ\text{C}$ | |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ | |
| I_{DM} | Drain Current-Continuous@ Current-Pulsed | $T_c=25^\circ\text{C}$ | 340 | A |
| Mounted on Large Heat Sink | | | | |
| I_D | Drain Current-Continuous | $T_c=25^\circ\text{C}$ | 85 | A |
| | | $T_c=100^\circ\text{C}$ | 55 | A |
| P_D | Maximum Power Dissipation | 142 | W | |
| $R_{\theta JC}$ | Thermal Resistance-Junction to Case | 0.88 | $^\circ\text{C}/\text{W}$ | |
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient (Note 2) | 50 | $^\circ\text{C}/\text{W}$ | |
| Drain-Source Avalanche Ratings | | | | |
| EAS | Avalanche Energy, Single Pulsed (Note 5) | 200 | mJ | |



Electrical Characteristics ($T_j=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
|---|---|---|-----|------|-----------|------------------|
| Static Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise stated) | | | | | | |
| $V_{(\text{BR})\text{DSS}}$ | Drain-Source Breakdown Voltage | $V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$ | 150 | -- | -- | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{\text{DS}}=150\text{V}, V_{\text{GS}}=0\text{V}$ | -- | -- | 1 | μA |
| I_{GSS} | Gate-Body Leakage Current | $V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$ | -- | -- | ± 100 | nA |
| $V_{\text{GS}(\text{th})}$ | Gate Threshold Voltage | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$ | 3.0 | -- | 4.6 | V |
| $R_{\text{DS}(\text{on})}$ | Drain-Source On-State Resistance ^(Note 3) | $V_{\text{GS}}=10\text{V}, I_{\text{D}}=44\text{A}$ | -- | 7.4 | 9.3 | $\text{m}\Omega$ |
| Dynamic Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (unless otherwise stated) ^(Note 4) | | | | | | |
| C_{iss} | Input Capacitance | $V_{\text{DS}}=75\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$ | -- | 2800 | -- | pF |
| C_{oss} | Output Capacitance | | -- | 710 | -- | pF |
| C_{rss} | Reverse Transfer Capacitance | | -- | 17 | -- | pF |
| g_{FS} | Forward Transconductance | $V_{\text{DS}}=2\text{V}, I_{\text{D}}=20\text{A}$ | -- | 41 | -- | S |
| Q_g | Total Gate Charge | $V_{\text{DS}}=75\text{V}, I_{\text{D}}=44\text{A}, V_{\text{GS}}=10\text{V}$ | -- | 40 | -- | nC |
| Q_{gs} | Gate-Source Charge | | -- | 23 | -- | nC |
| Q_{gd} | Gate-Drain Charge | | -- | 6.6 | -- | nC |
| Switching Characteristics | | | | | | |
| $T_{\text{d}(\text{on})}$ | Turn-on Delay Time | $V_{\text{DD}}=75\text{V}, I_{\text{D}}=44\text{A}, R_{\text{G}}=3.0\Omega, V_{\text{GS}}=10\text{V}$ | -- | 24 | -- | ns |
| T_{r} | Turn-on Rise Time | | -- | 91 | -- | ns |
| $T_{\text{d}(\text{off})}$ | Turn-Off Delay Time | | -- | 27 | -- | ns |
| T_{f} | Turn-Off Fall Time | | -- | 32 | -- | ns |
| Source-Drain Diode Characteristics @ $T_j = 25^\circ\text{C}$ (unless otherwise stated) | | | | | | |
| I_{SD} | Source-Drain Current (Body Diode) ^(Note 2) | | -- | -- | 85 | A |
| V_{SD} | Forward on voltage ^(Note 3) | $I_{\text{s}}=44\text{A}, V_{\text{GS}}=0\text{V}$ | -- | -- | 1.4 | V |
| T_{rr} | Reverse Recovery Time | $T_j=25^\circ\text{C}, I_{\text{s}}=44\text{A}, \frac{di}{dt}=100\text{A}/\mu\text{s}$ | -- | 48 | -- | ns |
| Q_{rr} | Reverse Recovery Charge ^(Note 3) | | -- | 58 | -- | nC |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_j=25^\circ\text{C}, V_{\text{DD}}=50\text{V}, V_{\text{G}}=10\text{V}, L=0.5\text{mH}, R_g=25\Omega$

Typical Electrical and Thermal Characteristics

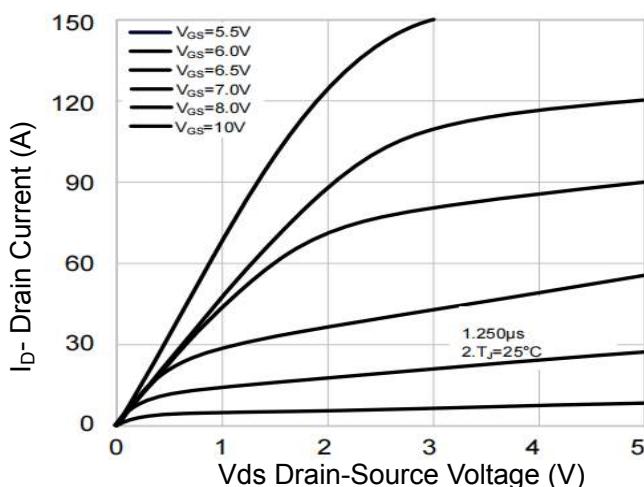


Figure 1 Output Characteristics

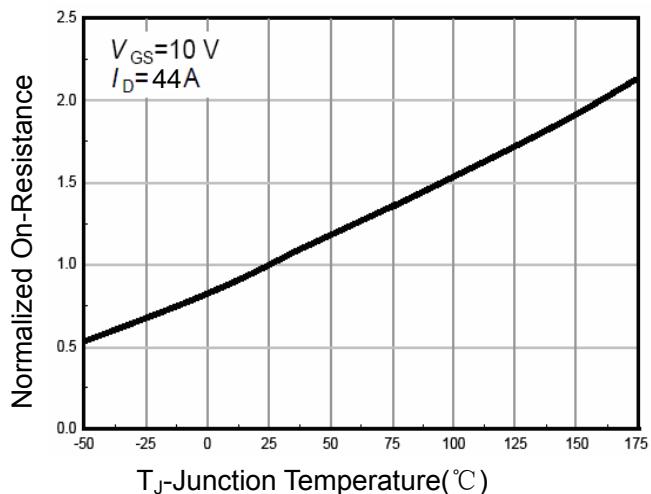


Figure 4 Rdson-JunctionTemperature

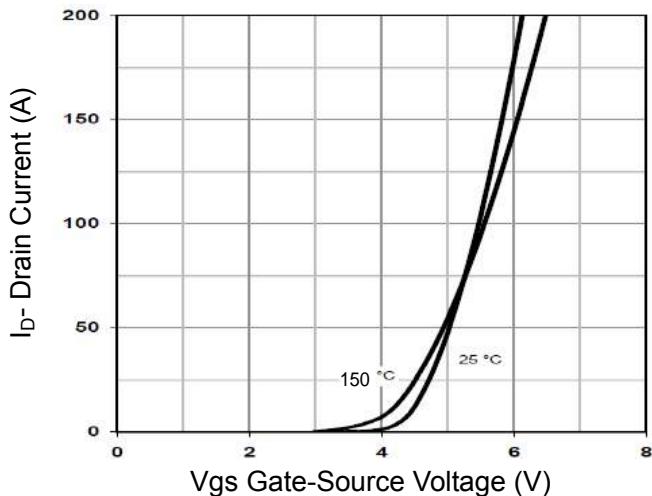


Figure 2 Transfer Characteristics

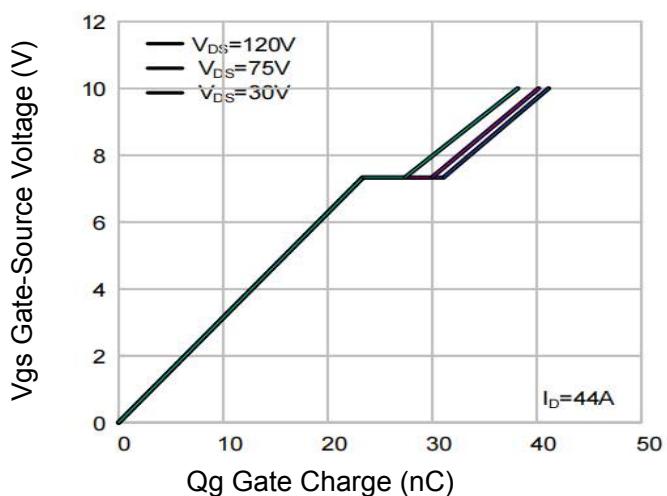


Figure 5 Gate Charge

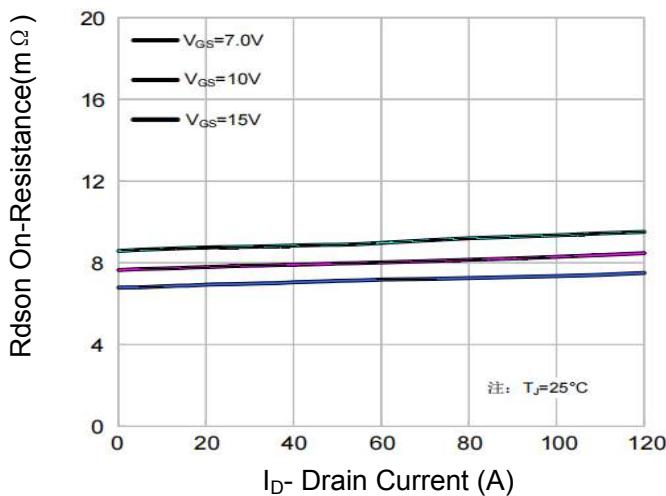


Figure 3 Rdson- Drain Current

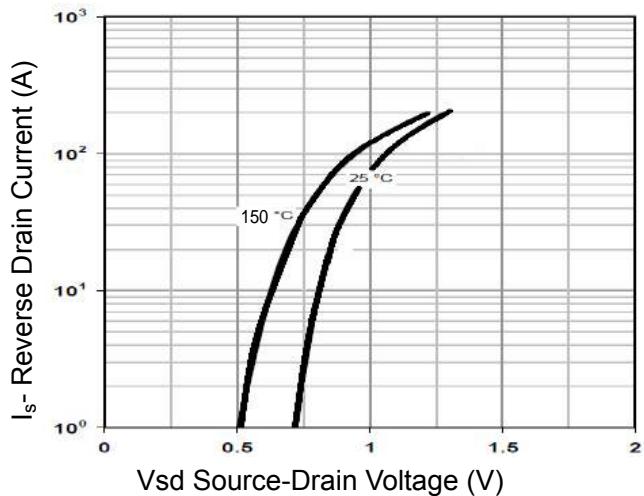


Figure 6 Source- Drain Diode Forward

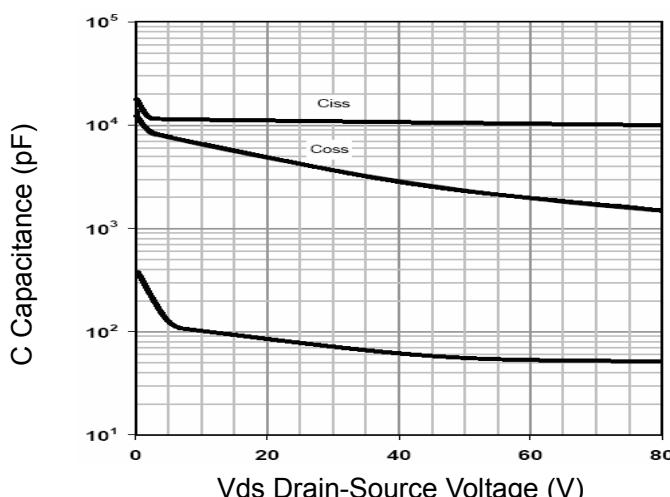


Figure 7 Capacitance vs Vds

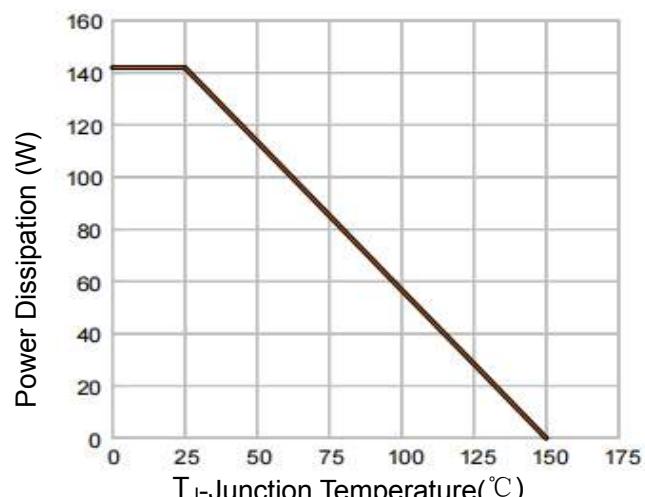


Figure 9 Power De-rating

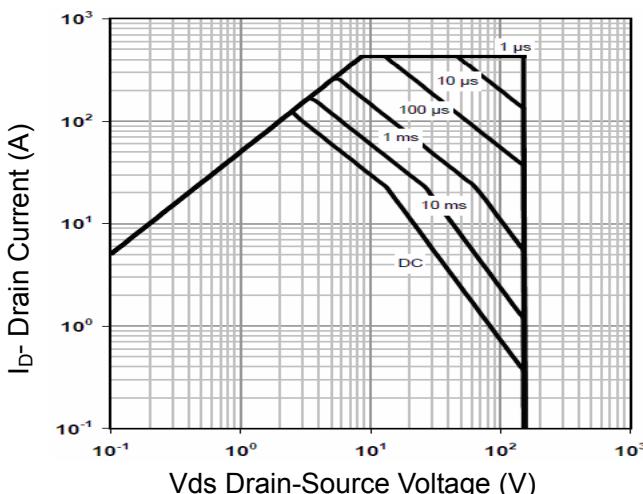


Figure 8 Safe Operation Area

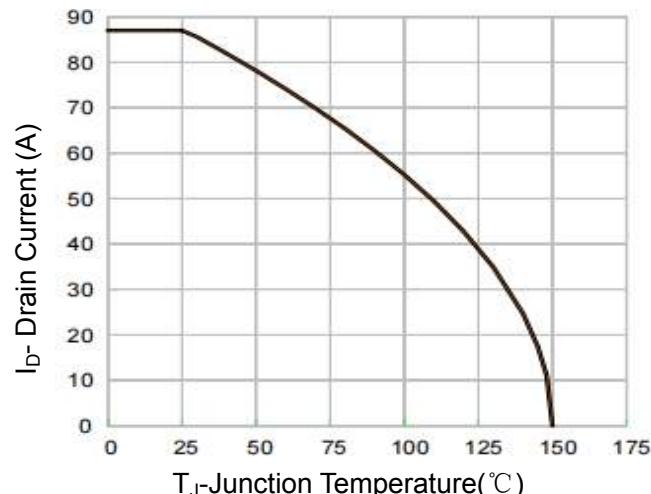


Figure 10 Current De-rating

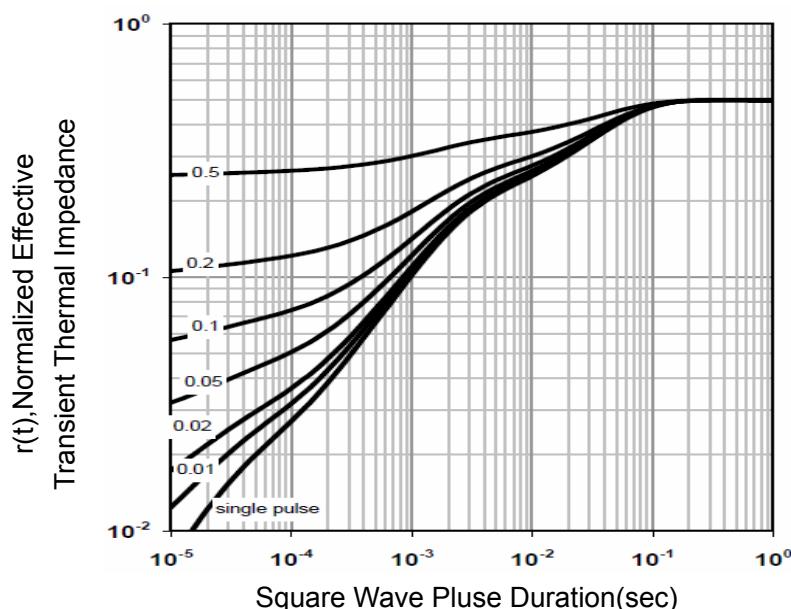
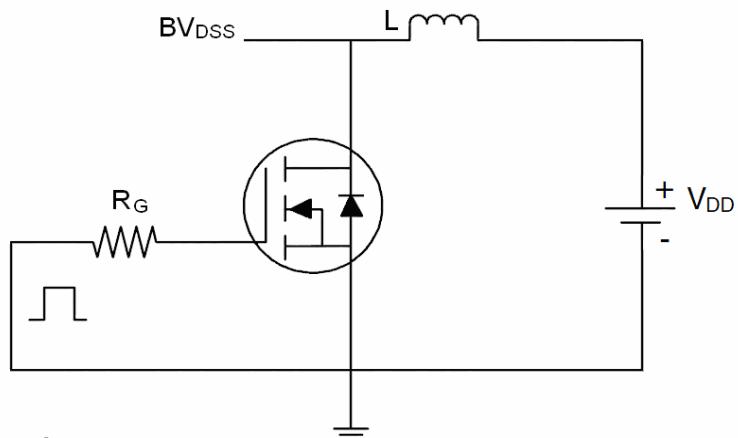


Figure 11 Normalized Maximum Transient Thermal Impedance

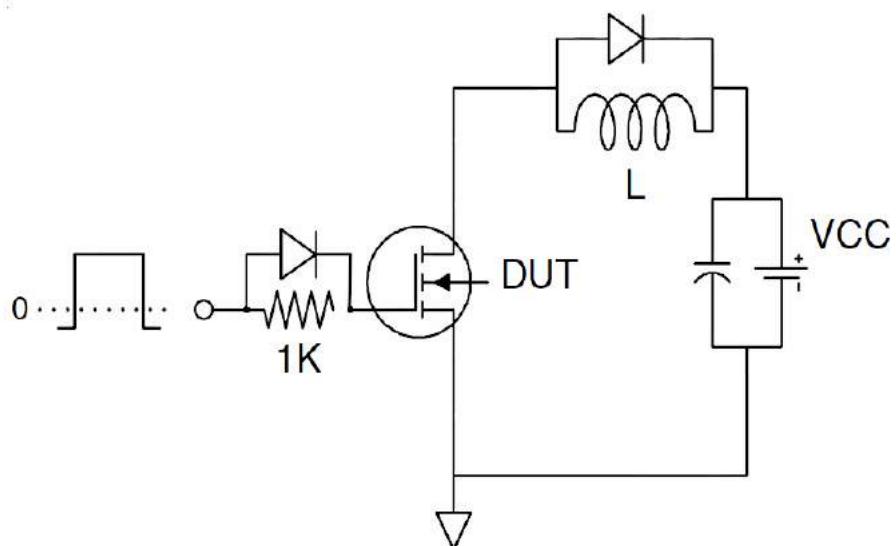


Test Circuit

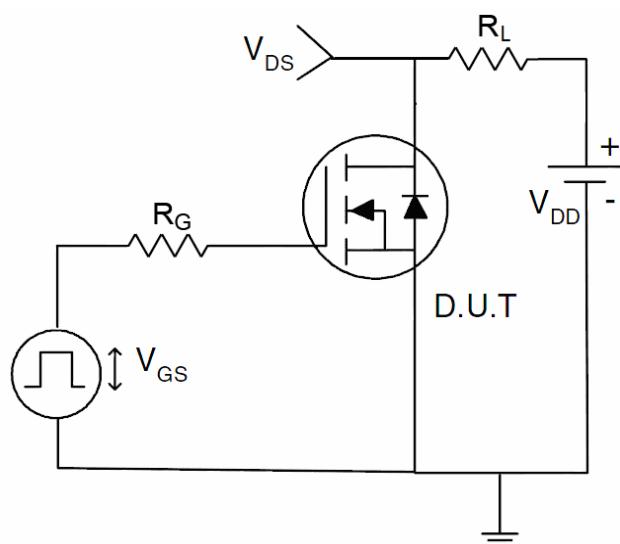
1) E_{AS} test Circuit



2) Gate charge test Circuit

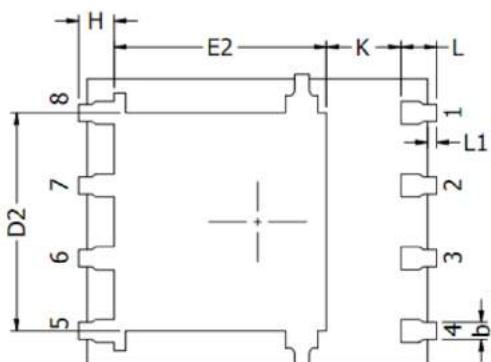


3) Switch Time Test Circuit

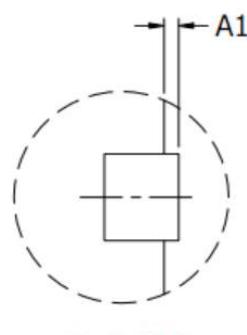
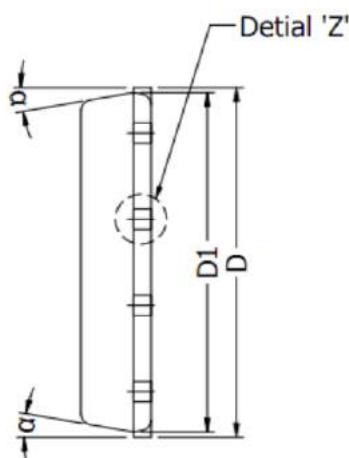
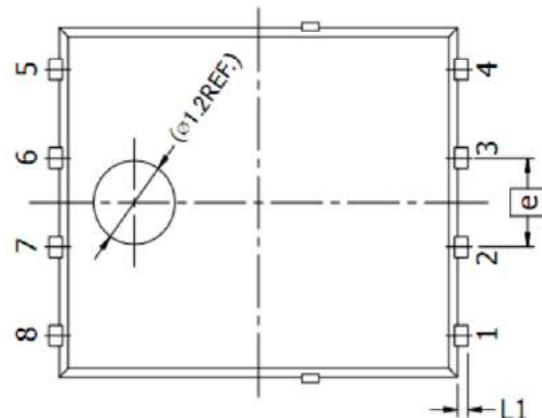




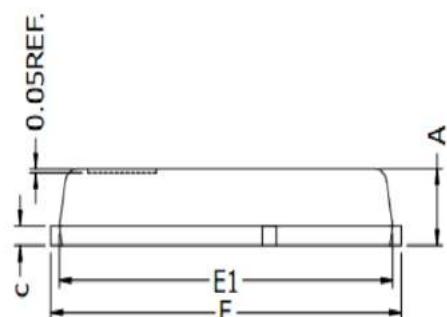
DFN5x6-8L Package Information



BACKSIDE VIEW



Detail 'Z'
Scale:4/1



| DIM. | MILLIMETERS | | |
|------|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0 | - | 0.05 |
| b | 0.30 | 0.40 | 0.50 |
| c | 0.20 | 0.25 | 0.30 |
| D | 5.15 BSC | | |
| D1 | 5.00 BSC | | |
| D2 | 3.76 | 3.81 | 3.86 |
| E | 6.15 BSC | | |
| E1 | 5.80 | 5.85 | 5.90 |
| E2 | 3.45 | 3.65 | 3.85 |
| e | 1.27 BSC | | |
| H | 0.51 | 0.61 | 0.71 |
| K | 1.10 | - | - |
| L | 0.51 | 0.61 | 0.71 |
| L1 | 0.08 | 0.15 | 0.23 |
| a | 10° | 11° | 12° |

Customer Service

Sales and Service:

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